

2SJ532

Silicon P Channel MOS FET

REJ03G0882-0400
(Previous: ADE-208-653B)
Rev.4.00
Sep 07, 2005

Description

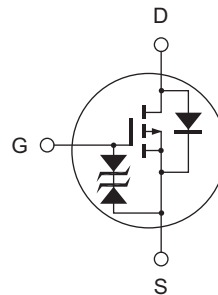
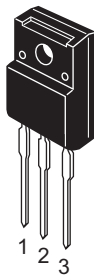
High speed power switching

Features

- Low on-resistance
 $R_{DS(on)} = 0.042 \Omega$ typ.
- Low drive current.
- 4 V gate drive devices.
- High speed switching.

Outline

RENESAS Package code: PRSS0003AE-A
(Package name: TO-220C•FM)



1. Gate
2. Drain
3. Source

Absolute Maximum Ratings

(Ta = 25°C)

Item	Symbol	Value	Unit
Drain to source voltage	V _{DSS}	-60	V
Gate to source voltage	V _{GSS}	±20	V
Drain current	I _D	-20	A
Drain peak current	I _{D (pulse)} ^{Note 1}	-80	A
Body to drain diode reverse drain current	I _{DR}	-20	A
Avalanche current	I _{AP} ^{Note 3}	-20	A
Avalanche energy	E _{AR} ^{Note 3}	34	mJ
Channel dissipation	P _{ch} ^{Note 2}	30	W
Channel temperature	T _{ch}	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

- Notes: 1. PW ≤ 10 μs, duty cycle ≤ 1%
 2. Value at T_c = 25°C
 3. Value at T_{ch} = 25°C, R_g ≥ 50 Ω

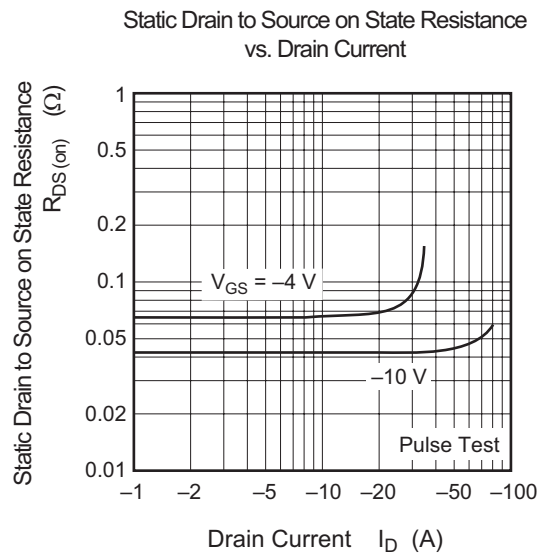
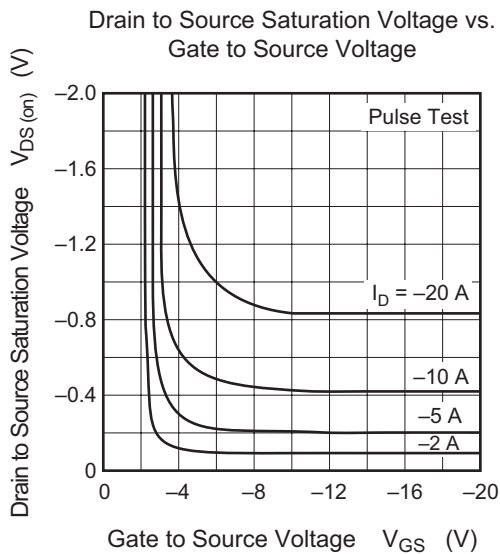
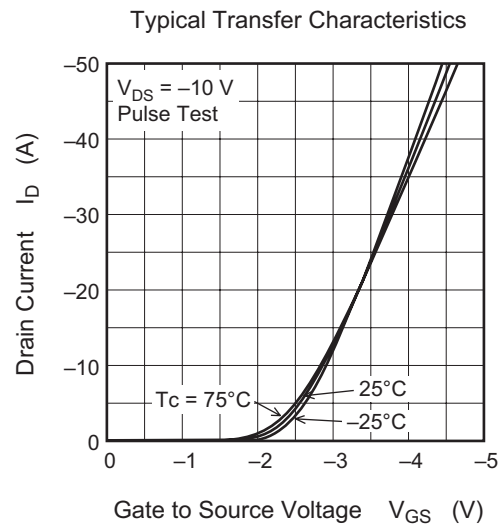
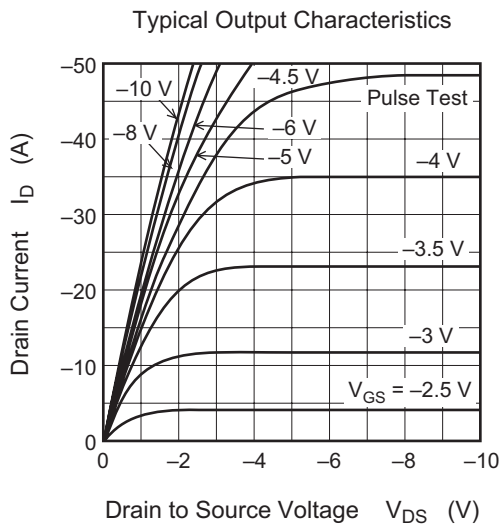
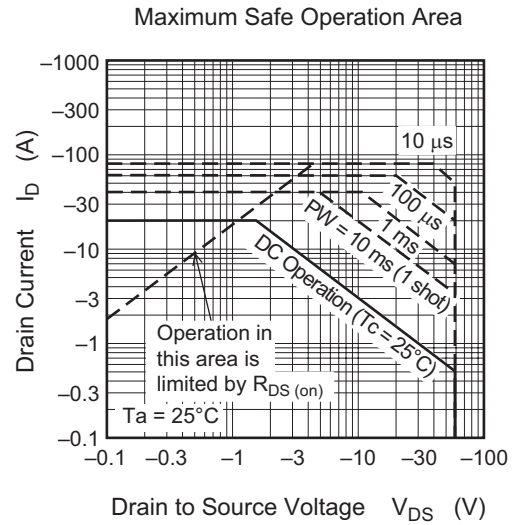
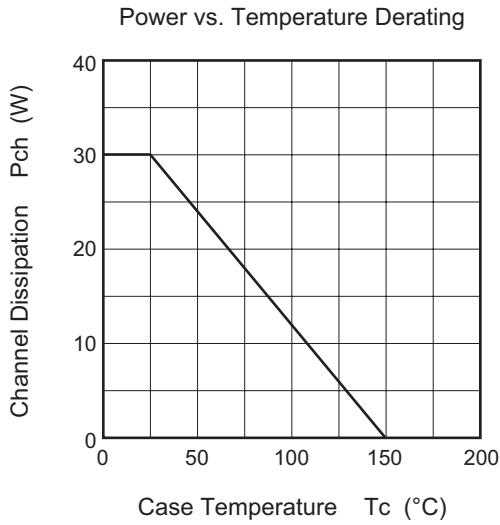
Electrical Characteristics

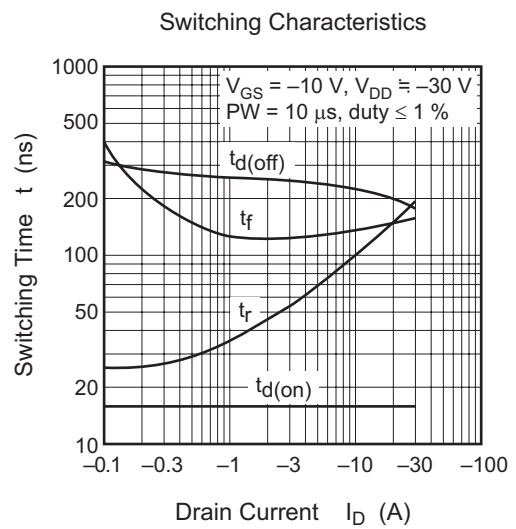
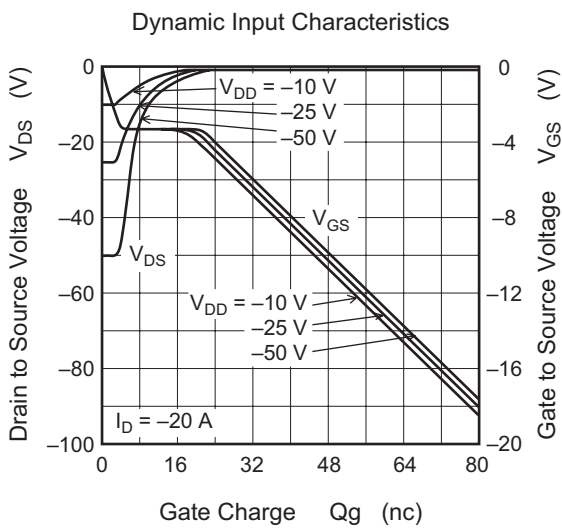
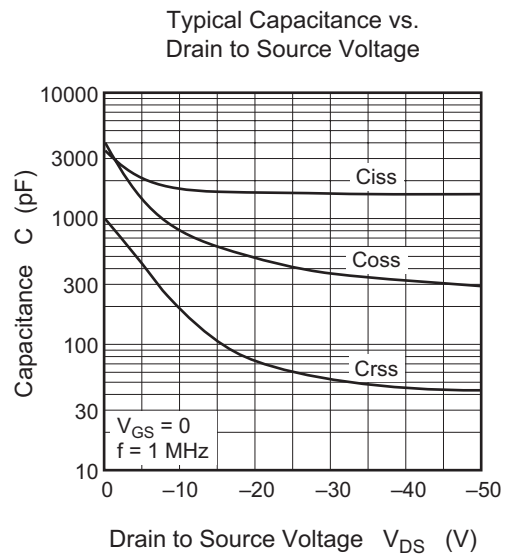
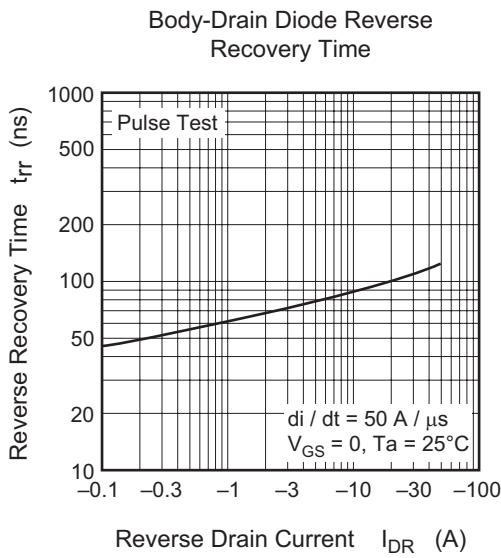
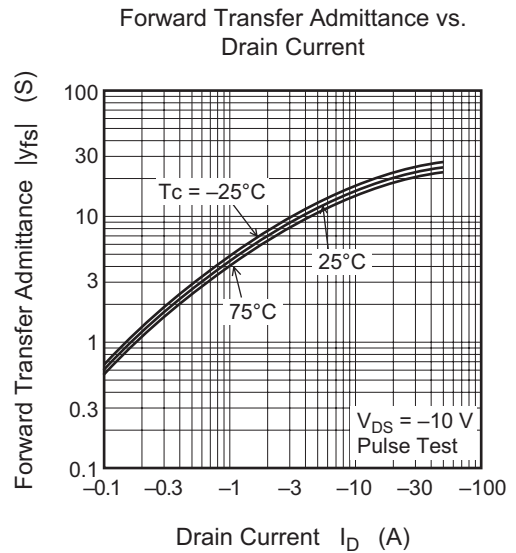
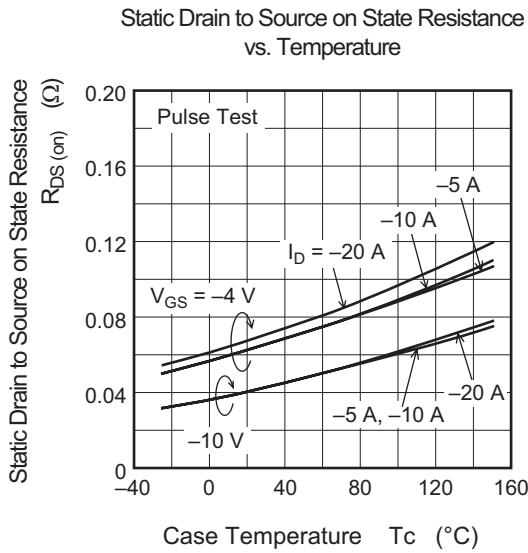
(Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain to source breakdown voltage	V _{(BR) DSS}	-60	—	—	V	I _D = -10 mA, V _{GS} = 0
Gate to source breakdown voltage	V _{(BR) GSS}	±20	—	—	V	I _G = ±100 μA, V _{DS} = 0
Zero gate voltage drain current	I _{DSS}	—	—	-10	μA	V _{DS} = -60 V, V _{GS} = 0
Gate to source leak current	I _{GSS}	—	—	±10	μA	V _{GS} = ±16 V, V _{DS} = 0
Gate to source cutoff voltage	V _{GS (off)}	-1.0	—	-2.0	V	I _D = -1 mA, V _{DS} = -10 V
Static drain to source on state resistance	R _{DS (on)}	—	0.042	0.055	Ω	I _D = -10 A, V _{GS} = -10 V ^{Note 4}
	R _{DS (on)}	—	0.065	0.095	Ω	I _D = -10 A, V _{GS} = -4 V ^{Note 4}
Forward transfer admittance	y _{fs}	10	16	—	S	I _D = -10 A, V _{DS} = -10 V ^{Note 4}
Input capacitance	C _{iss}	—	1750	—	pF	V _{DS} = -10 V
Output capacitance	C _{oss}	—	800	—	pF	V _{GS} = 0
Reverse transfer capacitance	C _{rss}	—	180	—	pF	f = 1 MHz
Turn-on delay time	t _{d (on)}	—	16	—	ns	V _{GS} = -10 V
Rise time	t _r	—	100	—	ns	I _D = -10 A
Turn-off delay time	t _{d (off)}	—	230	—	ns	R _L = 3 Ω
Fall time	t _f	—	140	—	ns	
Body to drain diode forward voltage	V _{DF}	—	-1.0	—	V	I _F = -20 A, V _{GS} = 0
Body to drain diode reverse recovery time	t _{rr}	—	100	—	ns	I _F = -20 A, V _{GS} = 0 di _F /dt = 50 A/μs

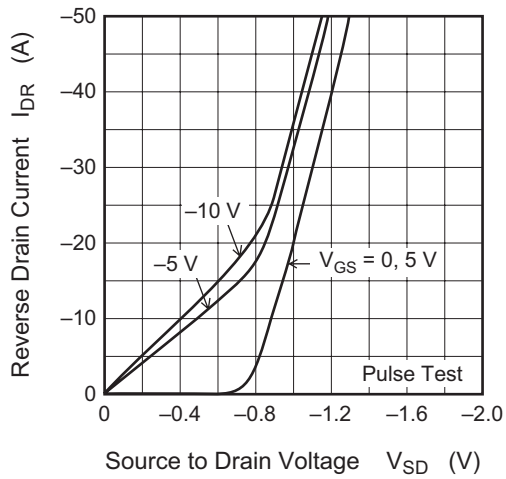
- Note: 4. Pulse test

Main Characteristics

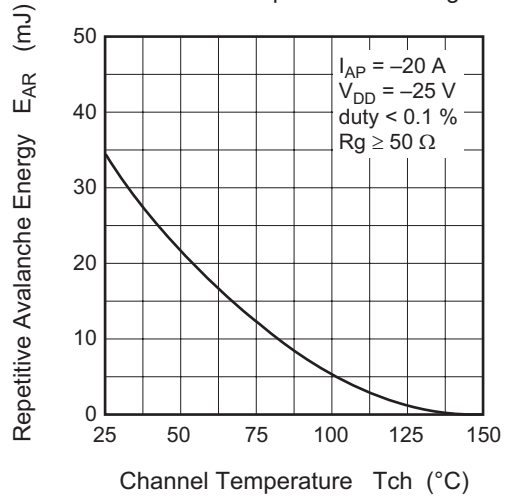




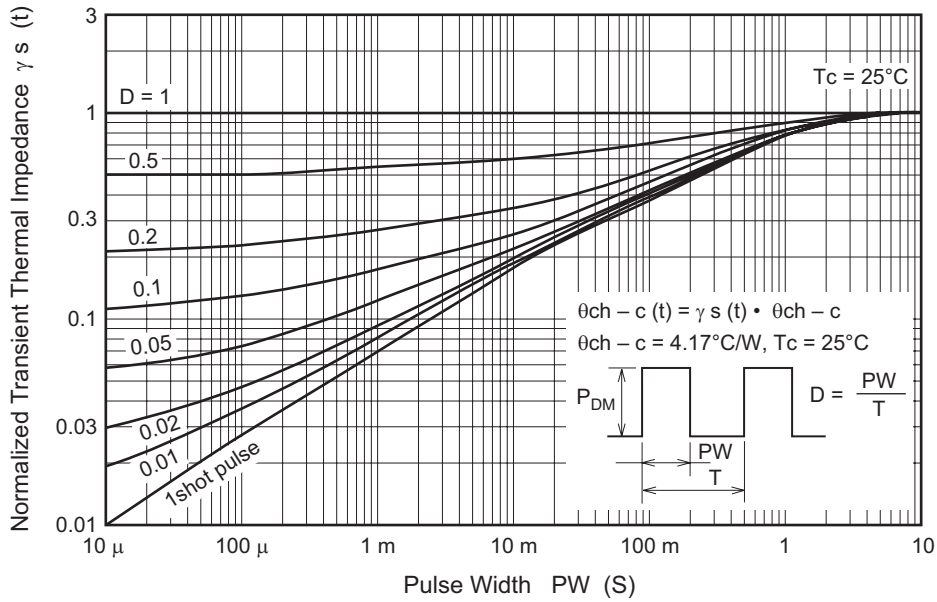
Reverse Drain Current vs. Source to Drain Voltage



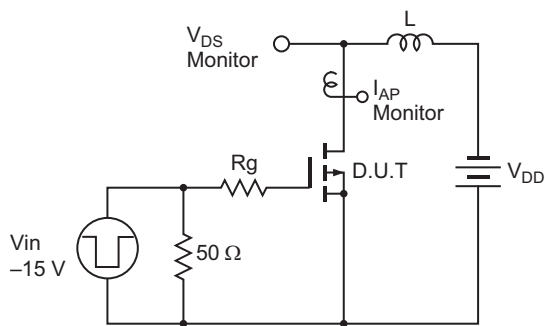
Maximum Avalanche Energy vs. Channel Temperature Derating



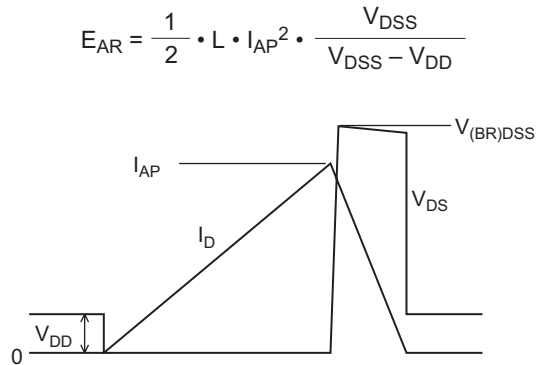
Normalized Transient Thermal Impedance vs. Pulse Width

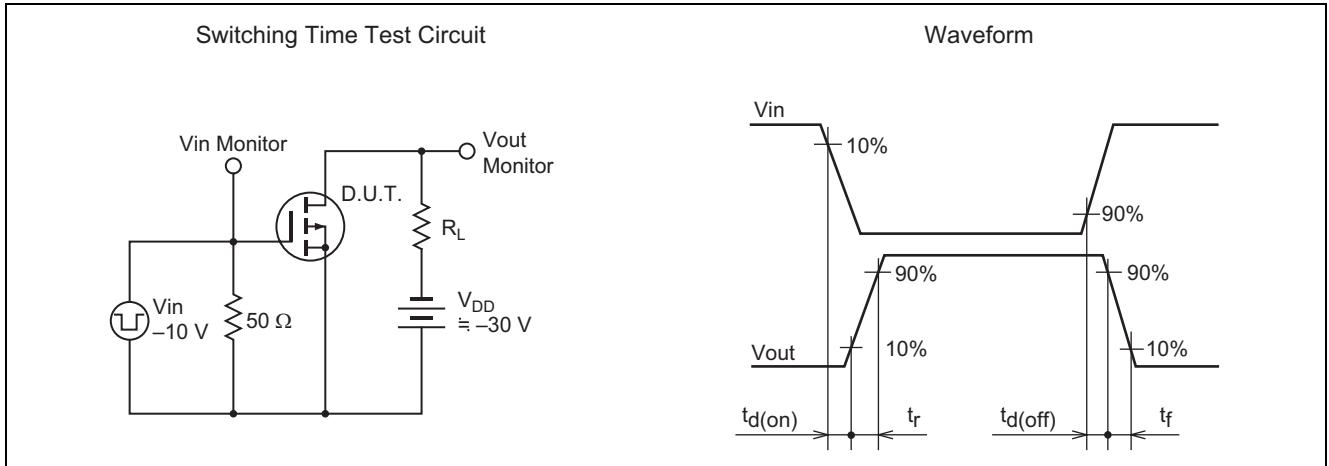


Avalanche Test Circuit

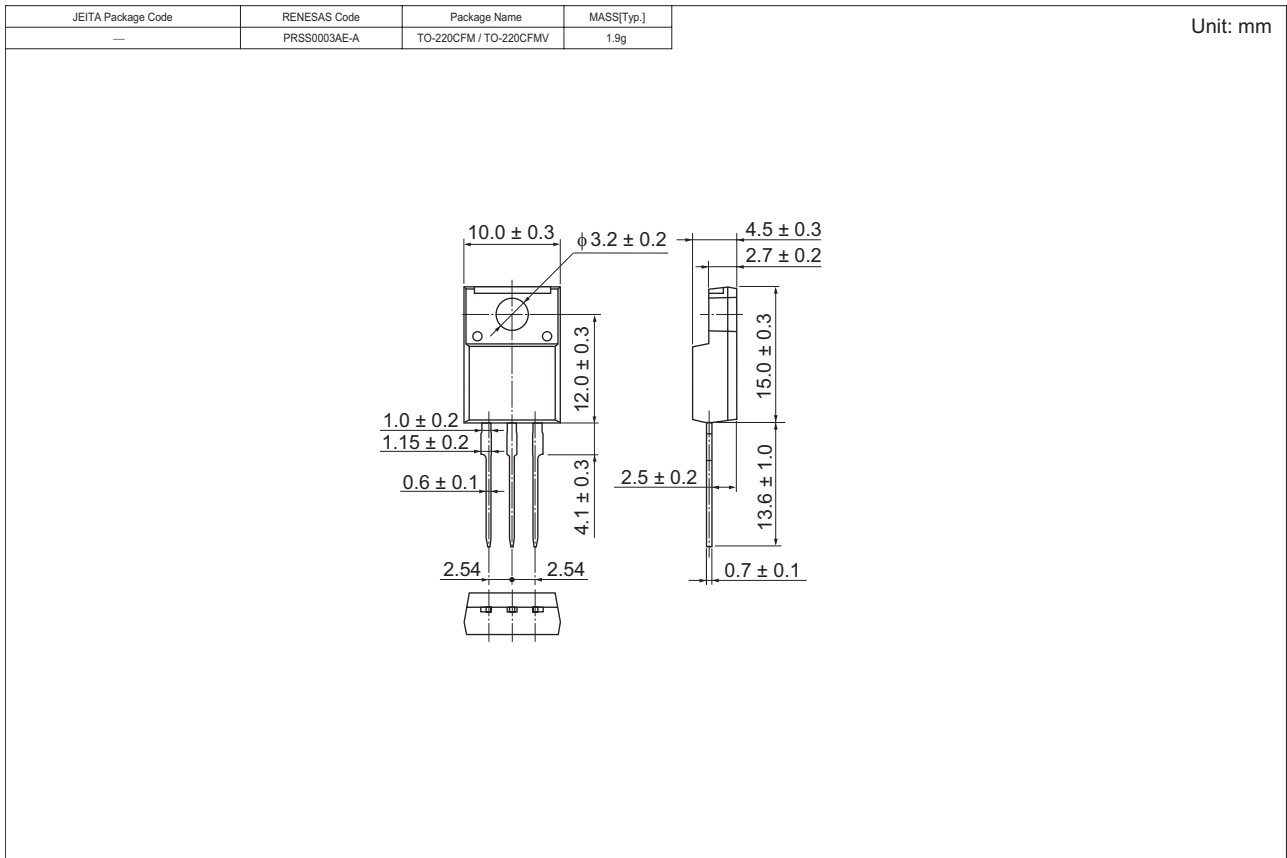


Avalanche Waveform





Package Dimensions



Ordering Information

Part Name	Quantity	Shipping Container
2SJ532-E	50 pcs	Plastic magazine

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.

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450 Holger Way, San Jose, CA 95134-1368, U.S.A
Tel: <1> (408) 382-7500, Fax: <1> (408) 382-7501

Renesas Technology Europe Limited

Dukes Meadow, Millboard Road, Bourne End, Buckinghamshire, SL8 5FH, U.K.
Tel: <44> (1628) 585-100, Fax: <44> (1628) 585-900

Renesas Technology Hong Kong Ltd.

7th Floor, North Tower, World Finance Centre, Harbour City, 1 Canton Road, Tsimshatsui, Kowloon, Hong Kong
Tel: <852> 2265-6688, Fax: <852> 2730-6071

Renesas Technology Taiwan Co., Ltd.

10th Floor, No.99, Fushing North Road, Taipei, Taiwan
Tel: <886> (2) 2715-2888, Fax: <886> (2) 2713-2999

Renesas Technology (Shanghai) Co., Ltd.

Unit2607 Ruijing Building, No.205 Maoming Road (S), Shanghai 200020, China
Tel: <86> (21) 6472-1001, Fax: <86> (21) 6415-2952

Renesas Technology Singapore Pte. Ltd.

1 Harbour Front Avenue, #06-10, Keppel Bay Tower, Singapore 098632
Tel: <65> 6213-0200, Fax: <65> 6278-8001

Renesas Technology Korea Co., Ltd.

Kukje Center Bldg. 18th Fl., 191, 2-ka, Hangang-ro, Yongsan-ku, Seoul 140-702, Korea
Tel: <82> 2-796-3115, Fax: <82> 2-796-2145

Renesas Technology Malaysia Sdn. Bhd.

Unit 906, Block B, Menara Amcorp, Amcorp Trade Centre, No.18, Jalan Persiaran Barat, 46050 Petaling Jaya, Selangor Darul Ehsan, Malaysia
Tel: <603> 7955-9390, Fax: <603> 7955-9510